



CPH6071 — NPN / PNP Epitaxial Planar Silicon Transistors

Video Output Driver, High-Frequency Amplifier Applications

Features

- Composite type with NPN transistor and PNP transistor contained in the conventional CPH package improving the mounting efficiency greatly.
- The CPH6071 is formed with two chips, being equivalent to the 2SC4504 and the other the 2SA1724, placed in one package.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[TR1(NPN Tr)]				
Collector-to-Base Voltage	V _{CB0}		30	V
Collector-to-Emitter Voltage	V _{CE0}		20	V
Emitter-to-Base Voltage	V _{EBO}		3	V
Collector Current	I _C		300	mA
Collector Current (Pulse)	I _{CP}		600	mA
Collector Dissipation	P _C	Mounted on a ceramic board (600mm ² ×0.8mm)	0.9	W
[TR2(PNP Tr)]				
Collector-to-Base Voltage	V _{CB0}		-30	V
Collector-to-Emitter Voltage	V _{CE0}		-20	V
Emitter-to-Base Voltage	V _{EBO}		-3	V
Collector Current	I _C		-300	mA
Collector Current (Pulse)	I _{CP}		-600	mA
Collector Dissipation	P _C	Mounted on a ceramic board (600mm ² ×0.8mm)	0.9	W
[Common Ratings]				
Total Dissipation	P _T	Mounted on a ceramic board (600mm ² ×0.8mm)	1.1	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Marking : GH

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CPH6071

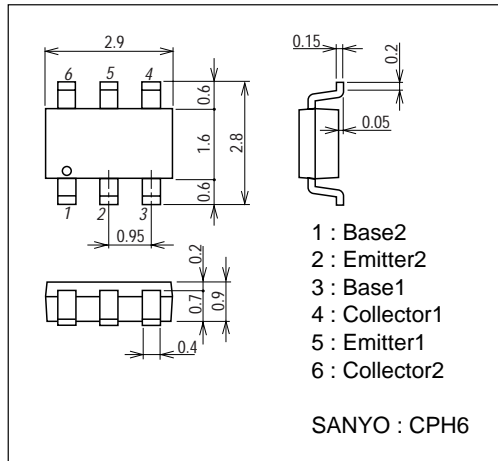
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[TR1(NPN Tr)]						
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0			0.1	μA
Emitter Cutoff Current	IEBO	V _{EB} =2V, I _C =0			5.0	μA
DC Current Gain	h _{FE} (1)	V _{CE} =5V, I _C =50mA	100		200	
	h _{FE} (2)	V _{CE} =5V, I _C =300mA	20			
Gain-Bandwidth Product	f _T	V _{CE} =5V, I _C =50mA		2.2		GHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		2.9		pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =10V, f=1MHz		2.6		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA		0.15	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA		0.9	1.2	V
[TR2(PNP Tr)]						
Collector Cutoff Current	ICBO	V _{CB} =-20V, I _E =0			-0.1	μA
Emitter Cutoff Current	IEBO	V _{EB} =-2V, I _C =0			-1.0	μA
DC Current Gain	h _{FE} (1)	V _{CE} =-5V, I _C =-50mA	15		100	
	h _{FE} (2)	V _{CE} =-5V, I _C =-300mA	5			
Gain-Bandwidth Product	f _T	V _{CE} =-5V, I _C =-100mA		1.5		GHz
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		4.9		pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =-10V, f=1MHz		4.4		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-0.4	-1.0	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA		-0.9	-1.2	V

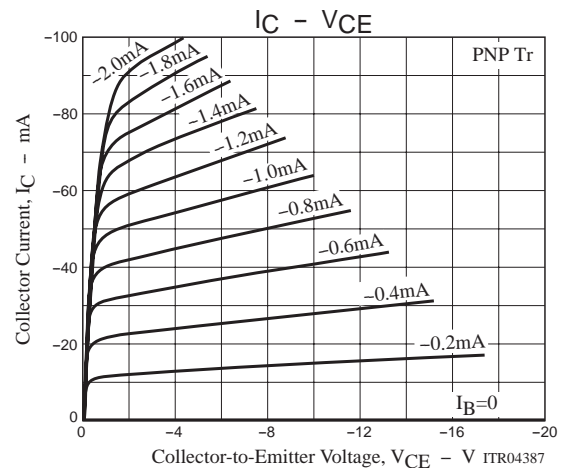
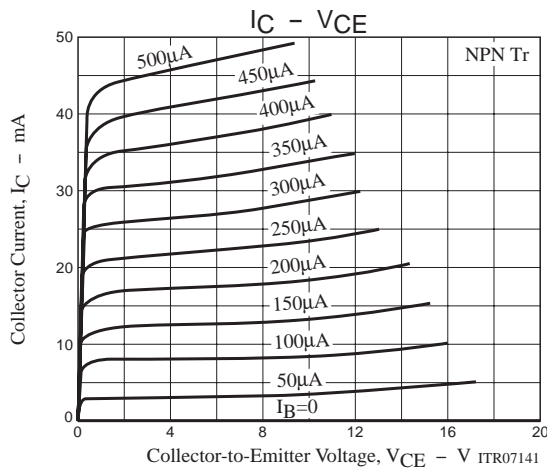
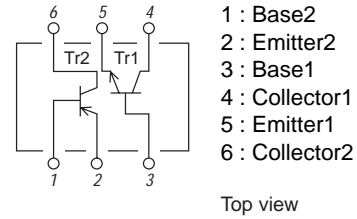
Package Dimensions

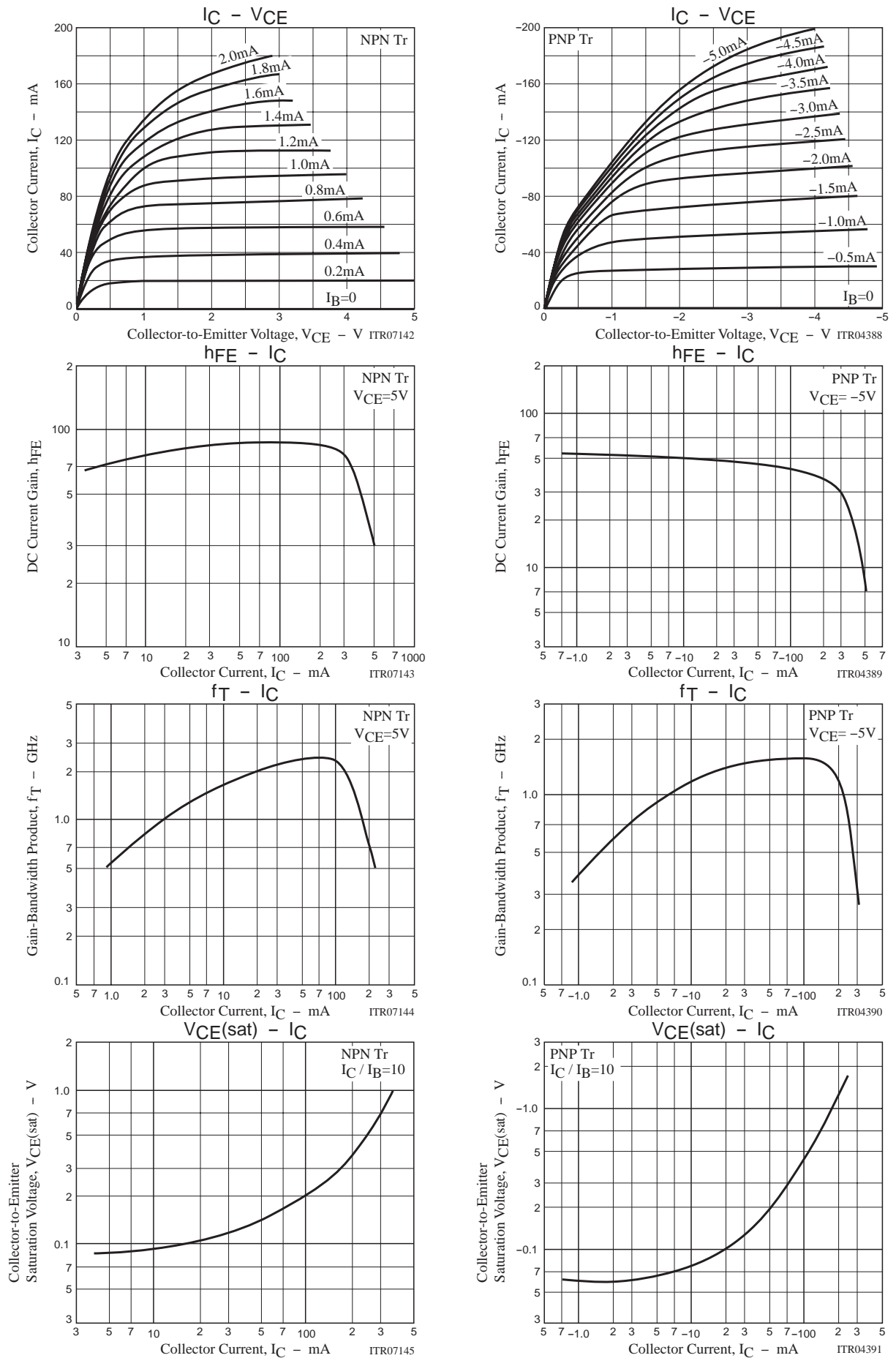
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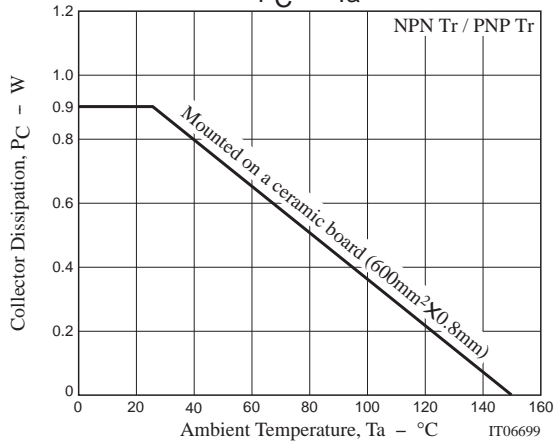
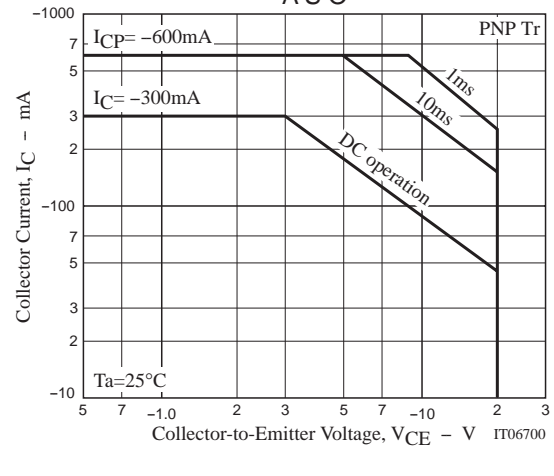
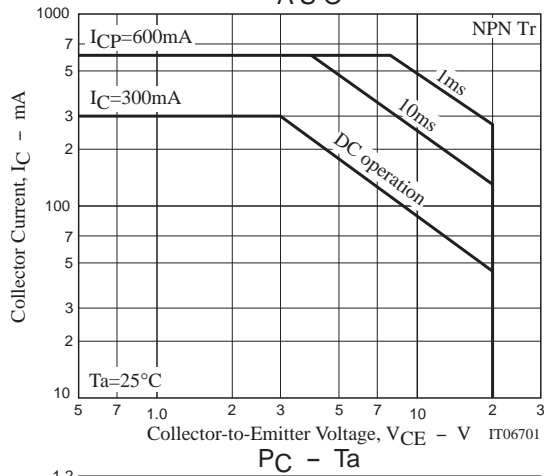
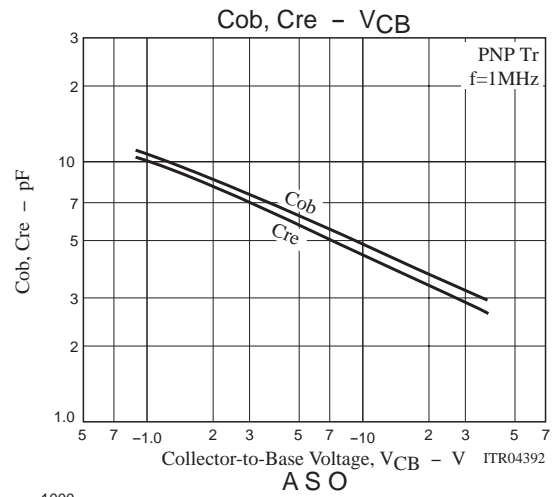
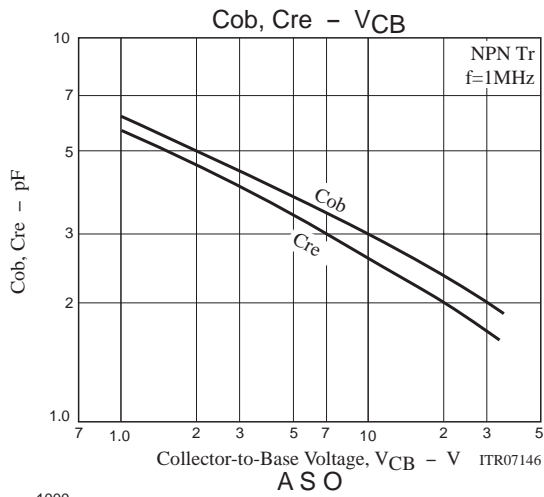
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Electrical Connection







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